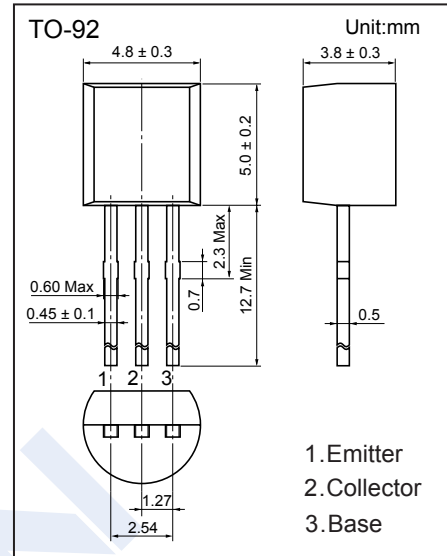


PNP Transistors

KTA1266

■ Features

- Excellent hFE Linearity
- Low Noise
- Complementary to KTC3198



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-50	V
Collector - Emitter Voltage	V _{CEO}	-50	
Emitter - Base Voltage	V _{EBO}	-5	
Collector Current - Continuous	I _C	-150	mA
Collector Power Dissipation	P _C	625	mW
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = -100uA, I _E =0	-50			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -1 mA, I _B =0	-50			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 uA, I _C =0	-5			
Collector-base cut-off current	I _{CB0}	V _{CB} = -50V, I _E =0			-0.1	uA
Emitter cut-off current	I _{EBO}	V _{EB} = 5V, I _C =0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100mA, I _B =-10mA			-0.3	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-100mA, I _B =-10mA			-1.1	
DC current gain	h _{FE(1)}	V _{CE} = -6V, I _C = -2mA	70		400	
	h _{FE(2)}	V _{CE} = -6V, I _C = -150mA	25			
Noise figure	NF	V _{CE} =-6V, I _C =-0.1mA, f=1KHZ, R _g =10KΩ			10	dB
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E =0, f=1MHz			7	pF
Transition frequency	f _t	V _{CE} = -10V, I _C = -1mA	80			MHz

■ Classification of h_{FE(1)}

Type	KTA1266-O	KTA1266-Y	KTA1266-G
Range	70-140	120-240	200-400

PNP Transistors

KTA1266

Typical Characteristics

